

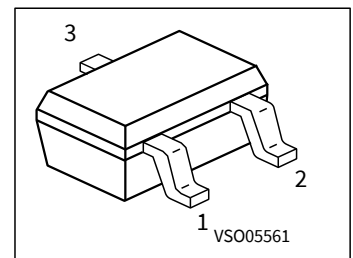
英飞凌SIPMOS®小信号晶体管

特性

- P沟道
- 增强模式
- 雪崩额定
- 逻辑电平
- dv/dt 额定
- 无铅镀层；符合 RoHS 标准
- 符合 AEC Q101 标准
- 符合 IEC61249-2-21 标准的无卤素

产品概述

Drain source voltage	V_{DS}	-60	V
Drain-source on-state resistance	$R_{DS(on)}$	8	Ω
Continuous drain current	I_D	-0.15	A



Type	Package	Tape and Reel	Marking	Pin 1	PIN 2	PIN 3
BSS84PW	PG-SOT-323	H6327:3000pcs/r.	YBs	G	S	D

除非另有规定，否则均为 $T_j = 25^\circ\text{C}$ 的 **最大额定值**。

Parameter	Symbol	Value	Unit
Continuous drain current $T_A = 25^\circ\text{C}$	I_D	-0.15	A
Pulsed drain current $T_A = 25^\circ\text{C}$	$I_{D \text{ puls}}$	-0.6	
Avalanche energy, single pulse $I_D = -0.15 \text{ A}$, $V_{DD} = -25 \text{ V}$, $R_{GS} = 25 \Omega$	E_{AS}	2.61	mJ
Avalanche energy, periodic limited by $T_{j\text{max}}$	E_{AR}	0.03	
Reverse diode dv/dt $I_S = -0.15 \text{ A}$, $V_{DS} = -48 \text{ V}$, $di/dt = 200 \text{ A}/\mu\text{s}$, $T_{j\text{max}} = 150^\circ\text{C}$	dv/dt	6	kV/ μs
Gate source voltage	V_{GS}	± 20	V
Power dissipation $T_A = 25^\circ\text{C}$	P_{tot}	0.3	W
Operating and storage temperature	T_j, T_{stg}	-55...+150	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1		55/150/56	
ESD Class JESF22-A114-HBM		Class 0	

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Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - soldering point (Pin 3)	R_{thJS}	-	-	110	K/W
SMD version, device on PCB:	R_{thJA}				
@ min. footprint		-	-	420	
@ 6 cm ² cooling area ¹⁾		-	-	350	

除非另有规定，否则均为 $T_j=25\text{ °C}$ 的电气特性。

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage $V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$	$V_{(BR)DSS}$	-60	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D = -20\text{ }\mu\text{A}$	$V_{GS(th)}$	-1	-1.5	-2	
Zero gate voltage drain current $V_{DS} = -60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 25\text{ }^{\circ}\text{C}$ $V_{DS} = -60\text{ V}$, $V_{GS} = 0\text{ V}$, $T_j = 125\text{ }^{\circ}\text{C}$	I_{DSS}	- -	-0.1 -10	-1 -100	μA
Gate-source leakage current $V_{GS} = -20\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	-	-10	-100	nA
Drain-source on-state resistance $V_{GS} = -2.7\text{ V}$, $I_D = -0.01\text{ A}$	$R_{DS(on)}$	-	10.5	25	Q
Drain-source on-state resistance $V_{GS} = -4.5\text{ V}$, $I_D = -0.12\text{ A}$	$R_{DS(on)}$	-	6.9	12	
Drain-source on-state resistance $V_{GS} = -10\text{ V}$, $I_D = -0.15\text{ A}$	$R_{DS(on)}$	-	4.6	8	

¹ 器件安装在 40 mm x 40 mm x 1.5 mm 环氧树脂 PCB FR4 上，漏极连接用铜面积为 6 cm²（一层，70 μm 厚）。印刷电路板垂直放置在静止空气中。

除非另有规定，否则均为 $T_j=25^\circ\text{C}$ 的电气特性。

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic Characteristics

Transconductance	g_{fs}	$V_{DS} < 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 0.15\text{A}$	0.08	0.16	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = -25\text{V}$, $f = 1\text{MHz}$	-	15.3	19.1	pF
Output capacitance	C_{oss}		-	5.8	7.3	
Reverse transfer capacitance	C_{rss}		-	3	3.8	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -30\text{V}$, $V_{GS} = -4.5\text{V}$, $I_D = -0.12\text{A}$, $R_G = 25\Omega$	-	6.7	10	ns
Rise time	t_r		-	16.2	24.3	
Turn-off delay time	$t_{d(off)}$		-	8.6	12.9	
Fall time	t_f		-	20.5	30.8	

Gate Charge Characteristics

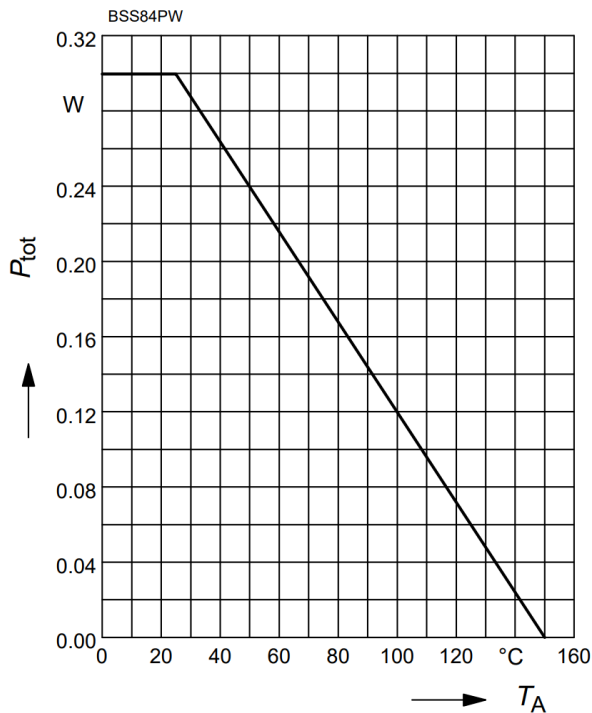
Gate to source charge	Q_{gs}	$V_{DD} = -48\text{V}$, $I_D = -0.15\text{A}$	-	0.25	0.38	nC
Gate to drain charge	Q_{gd}		-	0.3	0.45	
Gate charge total	Q_g	$V_{DD} = -48\text{V}$, $I_D = -0.15\text{A}$ $V_{GS} = 0$ to -10V	-	1	1.5	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = -48\text{V}$, $I_D = -0.15\text{A}$	-	-3.4	-	V

Reverse Diode

Inverse diode continuous forward current	I_S	$T_A = 25^\circ\text{C}$	-	-	-0.15	A
Inverse diode direct current, pulsed	I_{SM}		-	-	-0.6	
Inverse diode forward voltage	V_{SD}	$V_{GS} = 0\text{V}$, $I_F = -0.15\text{A}$	-	-0.84	-1.12	V
Reverse recovery time	t_{rr}	$V_R = -30\text{V}$, $I_F = I_S$, $di_F/dt = 100\text{A}/\mu\text{s}$	-	23.6	35.4	ns
Reverse recovery charge	Q_{rr}		-	11.6	17.4	nC

Power dissipation

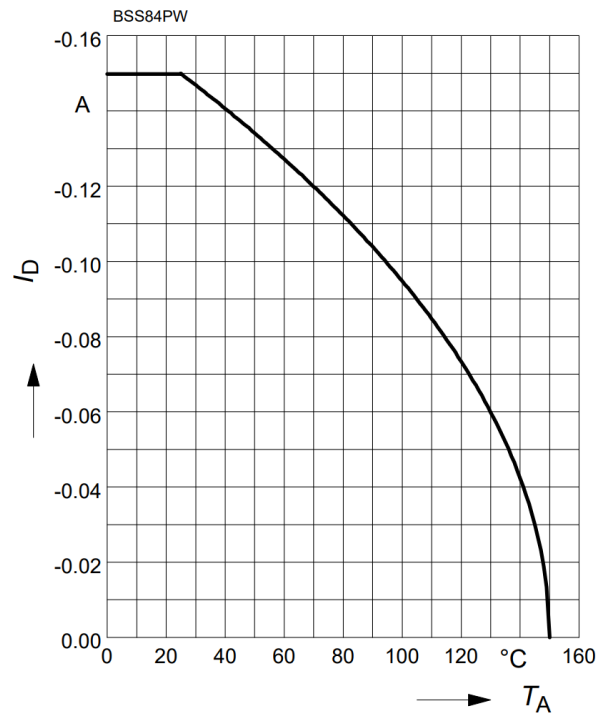
$$P_{\text{tot}} = f(T_A)$$



Drain current

$$I_D = f(T_A)$$

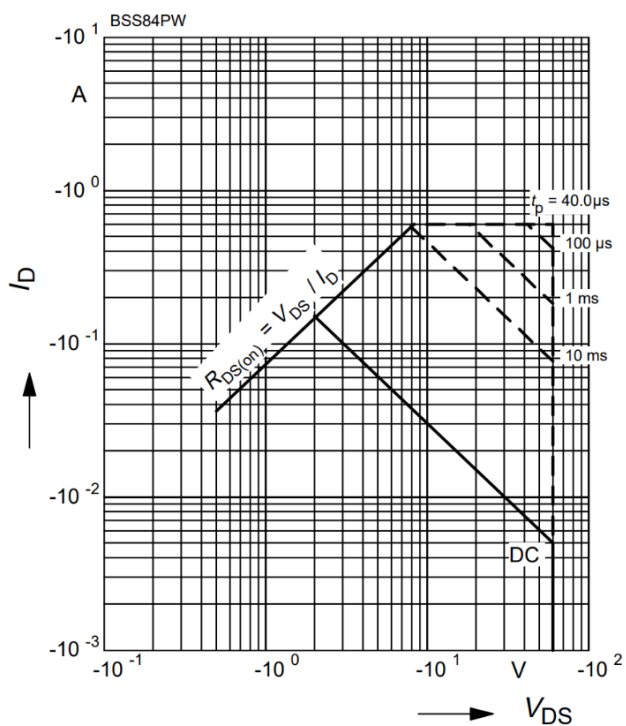
parameter: $V_{GS} \geq 10 \text{ V}$



Safe operating area

$$I_D = f(V_{DS})$$

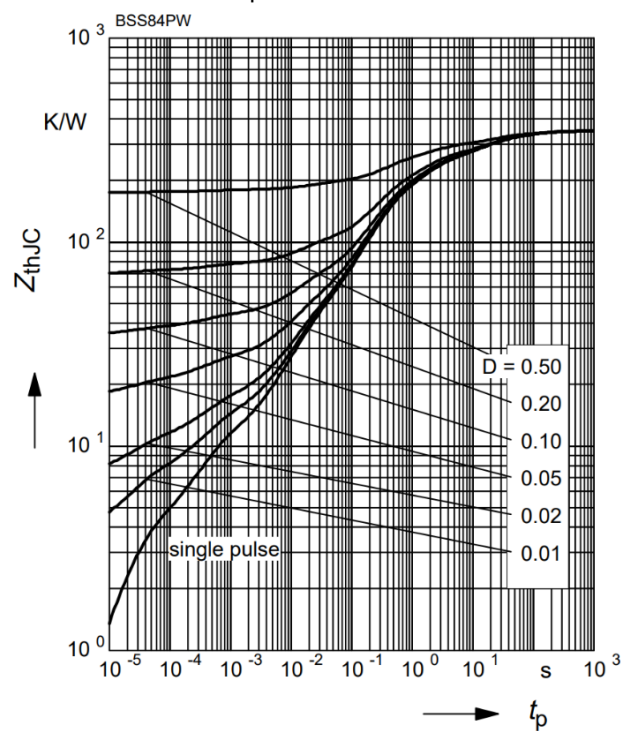
parameter: $D = 0$, $T_A = 25^\circ\text{C}$



Transient thermal impedance

$$Z_{thJC} = f(t_p)$$

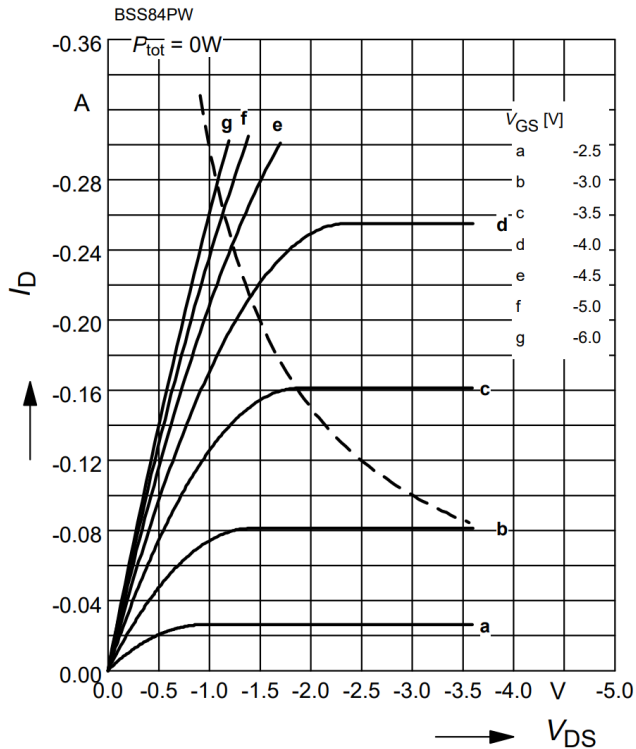
parameter: $D = t_p/T$



Typ. output characteristic

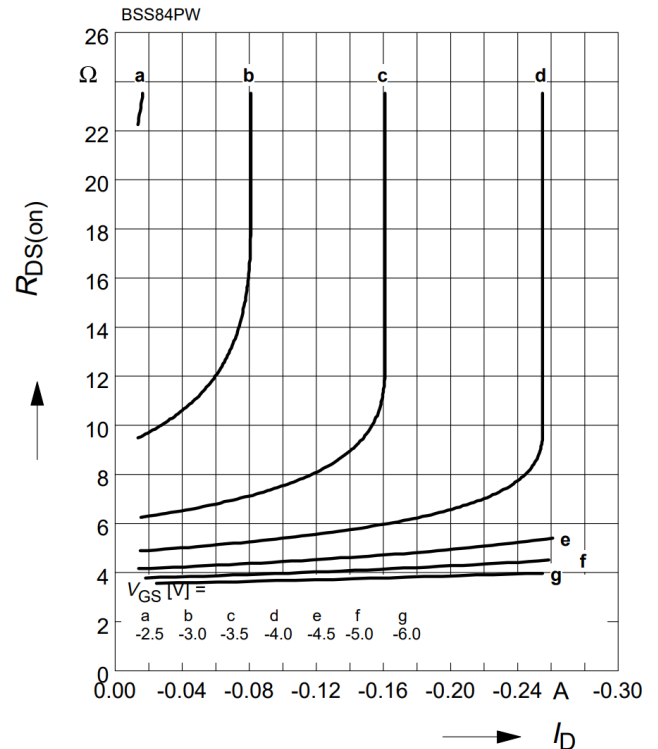
$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

parameter: $t_p = 80 \mu\text{s}$


Typ. drain-source-on-resistance

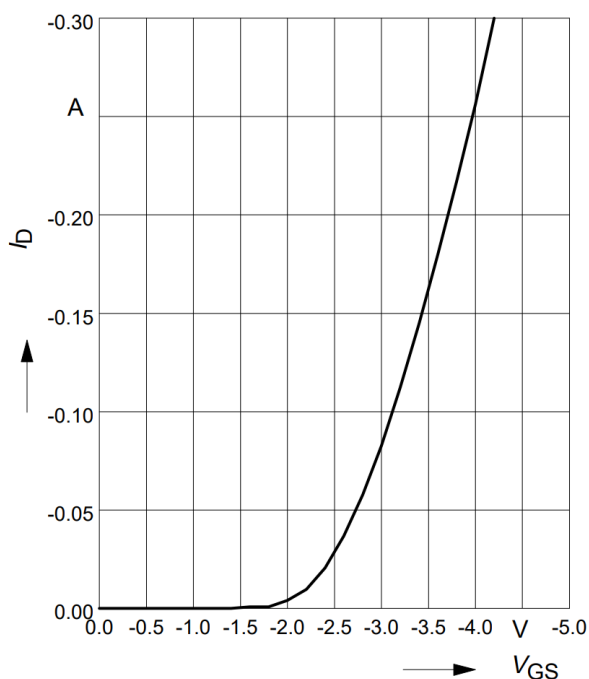
$$R_{DS(\text{on})} = f(I_D)$$

parameter: V_{GS}


Typ. transfer characteristics $I_D = f(V_{GS})$

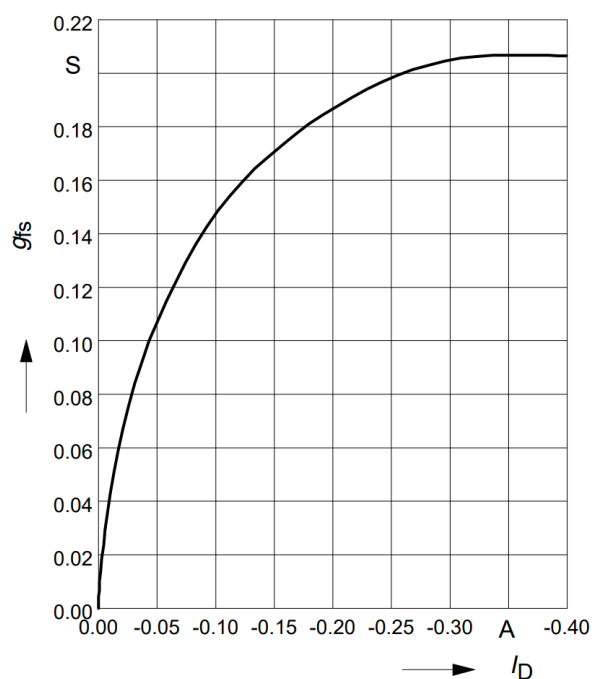
$$V_{DS} \geq 2 \times I_D \times R_{DS(\text{on})\text{max}}$$

parameter: $t_p = 80 \mu\text{s}$


Typ. forward transconductance

$$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$$

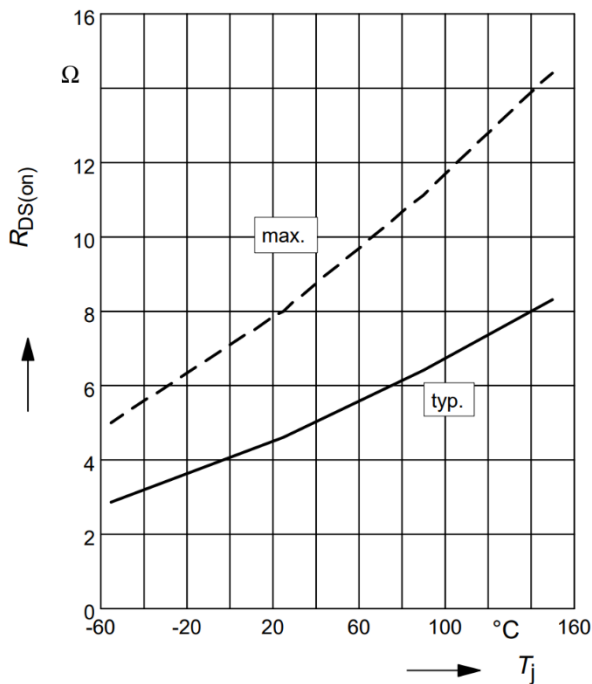
parameter: $= g_{fs}$



Drain-source on-resistance

$$R_{DS(on)} = f(T_j)$$

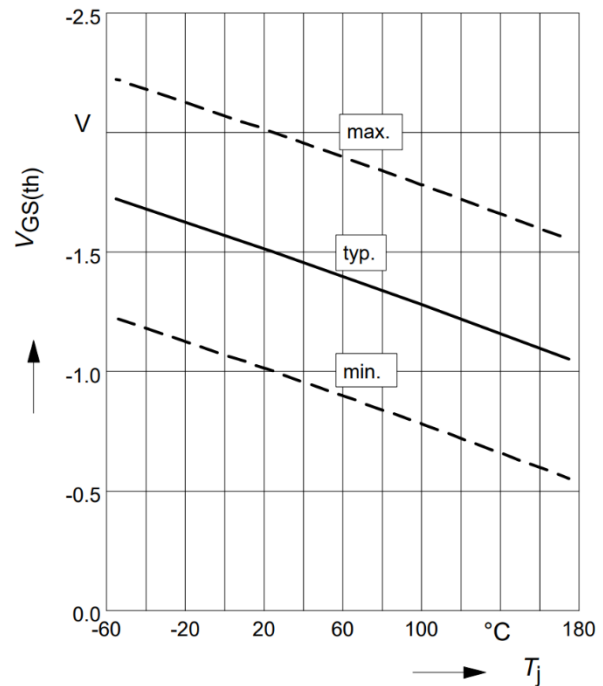
parameter: $I_D = -0.17 \text{ A}$, $V_{GS} = -10 \text{ V}$



Gate threshold voltage

$$V_{GS(th)} = f(T_j)$$

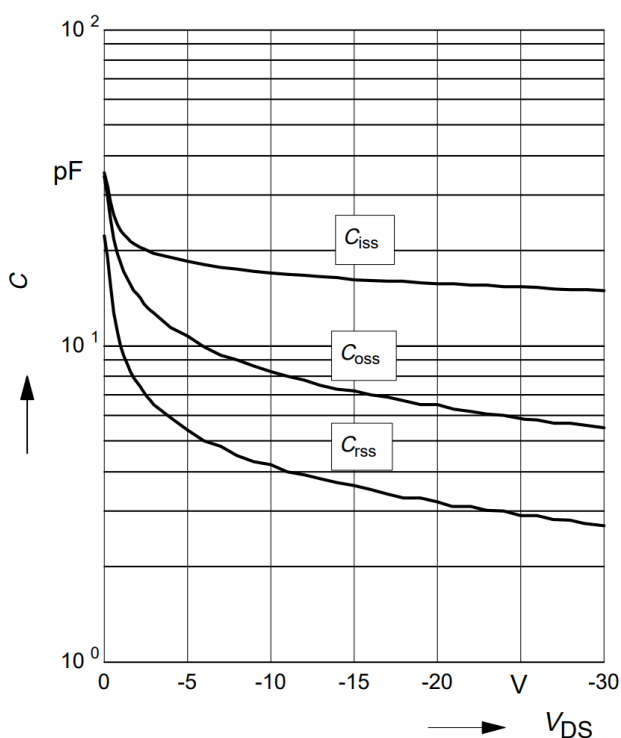
parameter: $V_{GS} = V_{DS}$, $I_D = -20 \mu\text{A}$



Typ. capacitances

$$C = f(V_{DS})$$

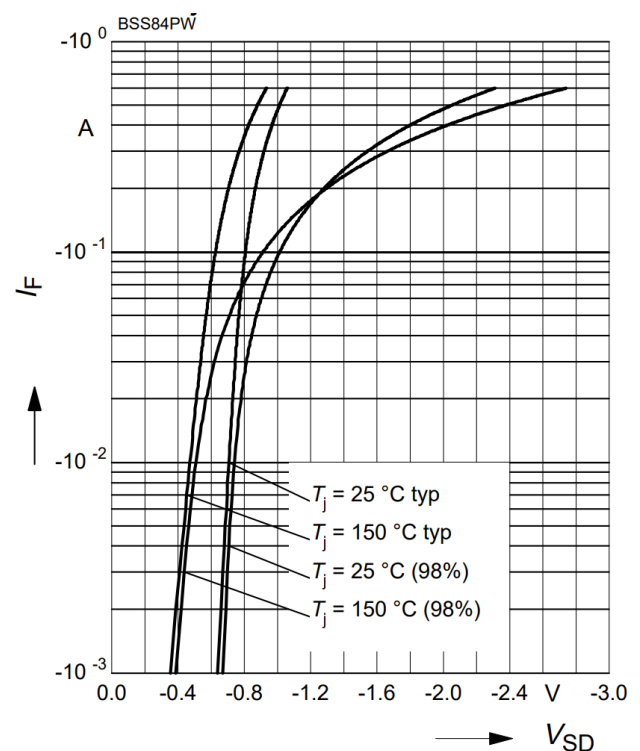
Parameter: $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$



Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

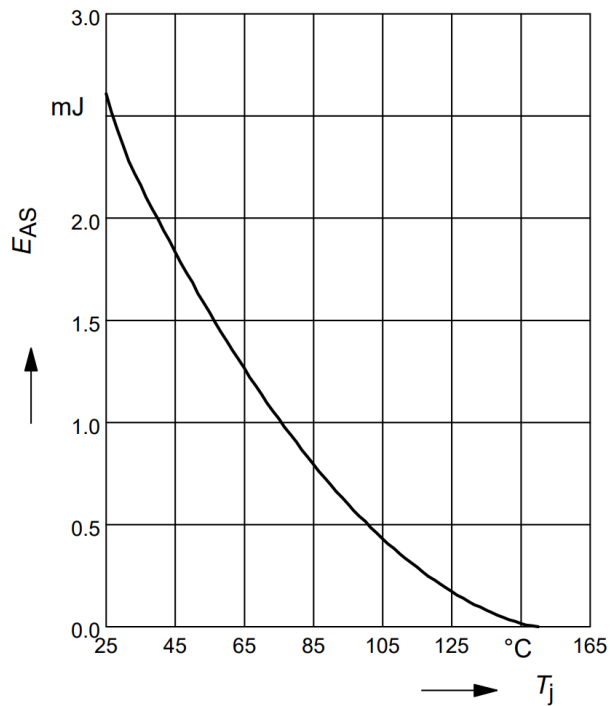
parameter: T_j , $t_p = 80 \mu\text{s}$



Avalanche energy

$$E_{AS} = f(T_j)$$

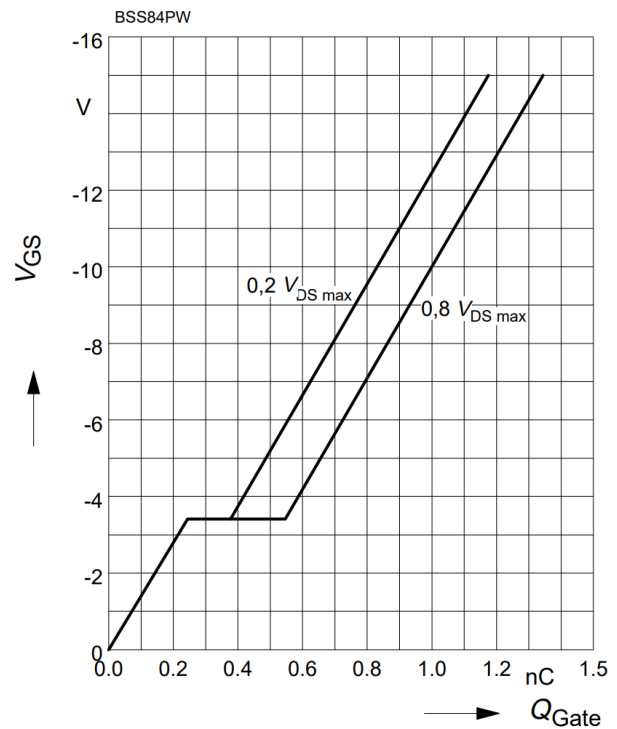
par.: $I_D = -0.15\text{ A}$, $V_{DD} = -25\text{ V}$, $R_{GS} = 25\ \Omega$



Typ. gate charge

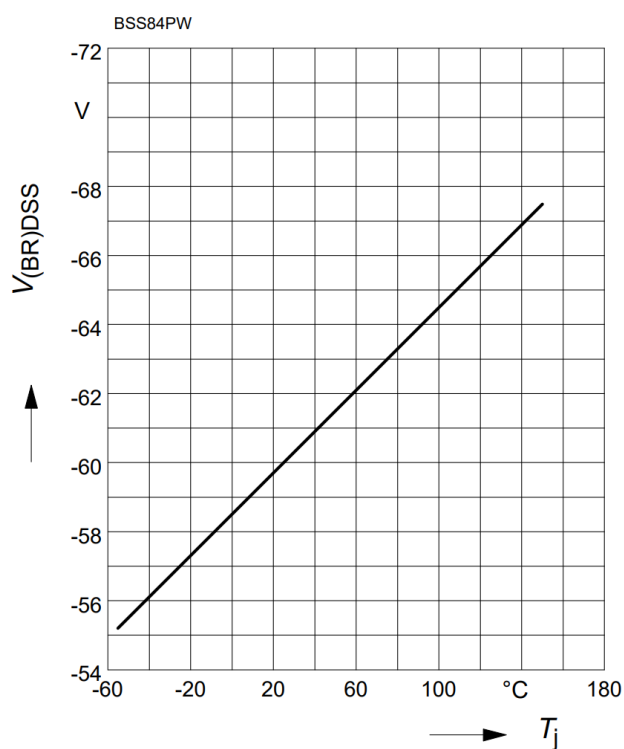
$$V_{GS} = f(Q_{Gate})$$

parameter: $I_D = -0.15\text{ A}$ pulsed

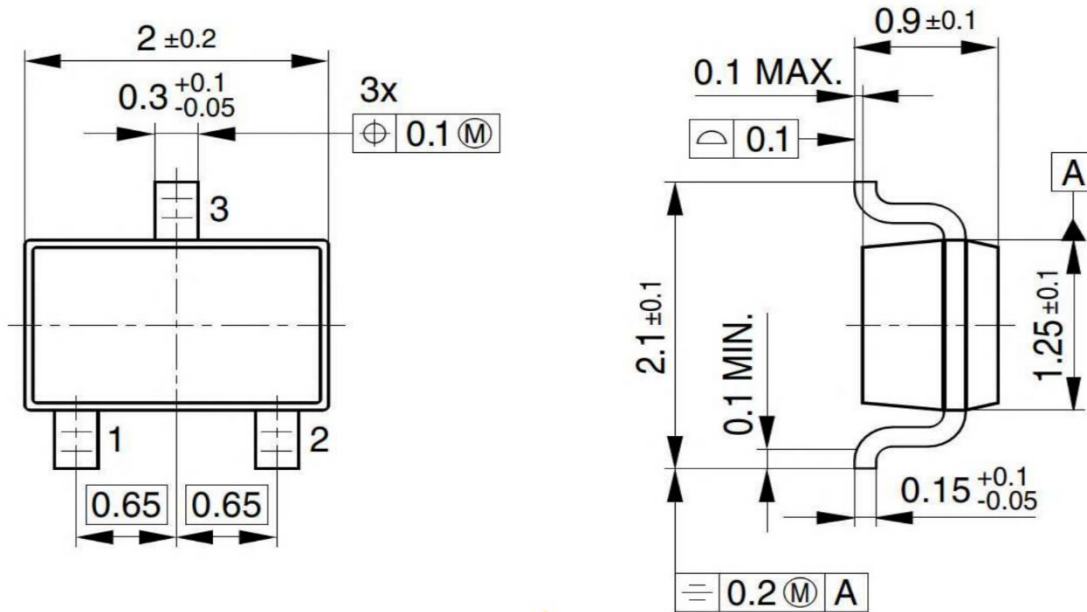


Drain-source breakdown voltage

$$V_{(BR)DSS} = f(T_j)$$

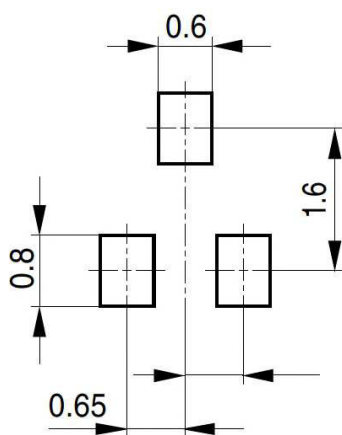


封装外形 SOT-323

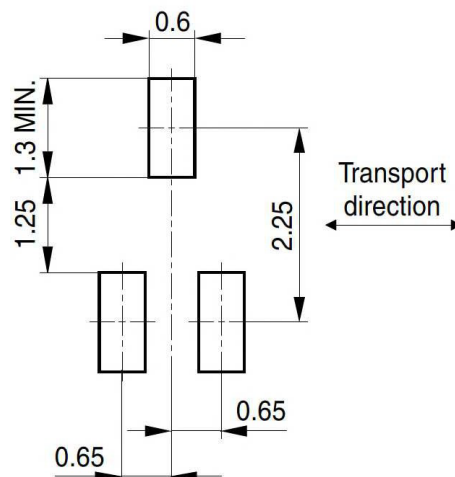


封装尺寸

焊接类型：回流焊接



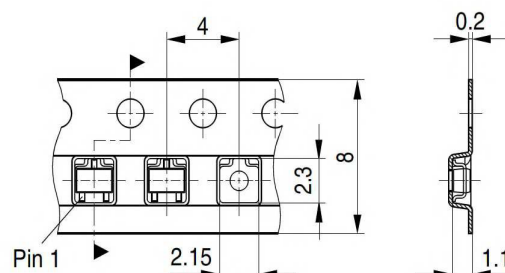
焊接类型：波峰焊接



卷带封装

Reel $\varnothing 180 \text{ mm}$: 3.000 Pieces/Reel
 Reels/Box: 1 x 3.000 = 3.000
 Reels/Box: 10 x 3.000 = 30.000

Reel $\varnothing 330 \text{ mm}$: 10.000 Pieces/Reel
 Reels/Box: 1 x 10.000 = 10.000



-60V SIPMOS 小信号晶体管

BSS84PW

修订记录

BSS84PW

Revision: 2016-06-27, Rev. 2.0

历史修订版本

Revision	Date	Subjects (major changes since last revision)
2.0	2016-06-27	Release of final version

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